

NCE Automotive P-Channel Enhancement Mode Power MOSFET

Description

The NCEA15P30K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. It is ESD protested.

General Features

● V_{DS} =-150V,I_D =-30A

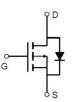
 $R_{DS(ON)}$ <88m Ω @ V_{GS} =-10V (Typ:78m Ω)

 $R_{DS(ON)}$ <95m Ω @ V_{GS} =-4.5V (Typ:81.5m Ω)

- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low On-Resistance
- Pb-free lead plating
- 100% UIS tested
- 100% ∆Vds tested
- AEC-Q101 qualified

Application

- Automotive application
- Portable equipment and battery powered systems



Schematic diagram



Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
A15P30K	A15P30K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	-150	V	
Gate-Source Voltage	V _G s	±20	V	
Drain Current-Continuous	I _D	-30	А	
Drain Current-Continuous(T _C =100 °C)	I _D (100°C)	-21.2	А	
Pulsed Drain Current	I _{DM}	-120	А	
Maximum Power Dissipation	P _D	180	W	
Single pulse avalanche energy (Note 5)	E _{AS}	338	mJ	
Derating factor		1.2	W/℃	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	°C	

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	R _{eJC}	0.83	°C/W	
Thermal Resistance,Junction-to-Ambient (Note 4)	R _{0JA}	50	°C/W	

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-150V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	,					
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.5	-1.8	-2.5	V
Dunin Course On State Besietenes		V _{GS} =-10V, I _D =-20A	-	78	88	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-20A	-	81.5	95	mΩ
Forward Transconductance	g FS	V _{DS} =-10V,I _D =-20A	-	50	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss	\/ 75\/\\ 0\/	-	6015	-	pF
Output Capacitance	Coss	V_{DS} =-75V, V_{GS} =0V,	-	117	-	pF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	85	-	pF
Switching Characteristics (Note 4)			'			
Turn-on Delay Time	t _{d(on)}		-	17	-	nS
Turn-on Rise Time	tr	V _{DD} =-75V,I _D =-20A	-	80	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =-10V, R_{GEN} =9.1 Ω	-	45	-	nS
Turn-Off Fall Time	t _f		-	65	-	nS
Total Gate Charge	Qg	.,,	-	124	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-75V,I _D =-20A,	-	20	-	nC
Gate-Drain Charge	Q_{gd}	- V _{GS} =-10V	-	28	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-20A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is	-	-	-	-30	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =-20A	-	90	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)} -$		145	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				

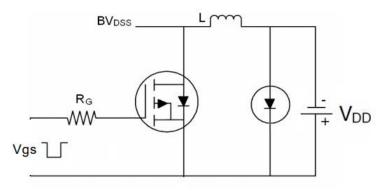
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. The value of R_{BJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150° C may be used if the PCB allows it.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

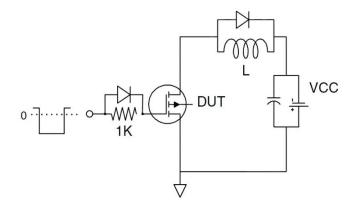


Test Circuit

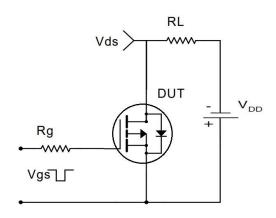
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

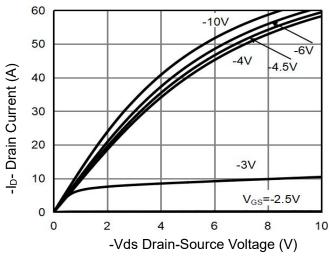


Figure 1 Output Characteristics

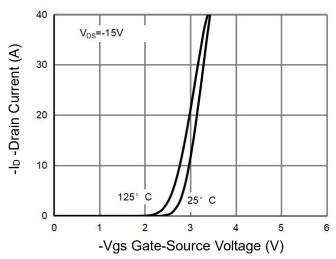


Figure 2 Transfer Characteristics

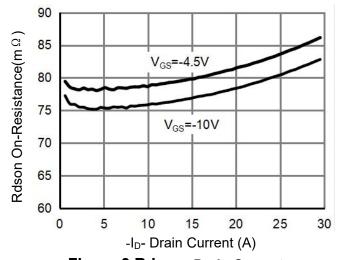


Figure 3 Rdson- Drain Current

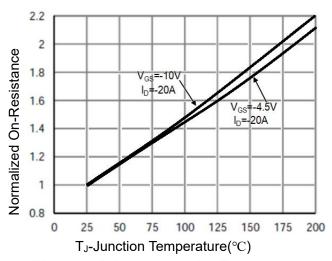


Figure 4 Rdson-JunctionTemperature

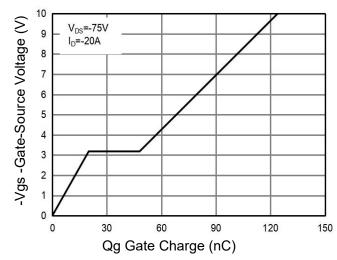


Figure 5 Gate Charge

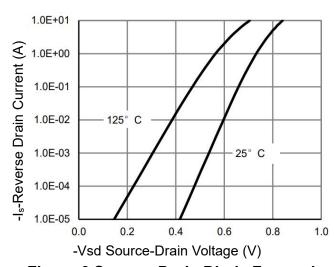


Figure 6 Source- Drain Diode Forward



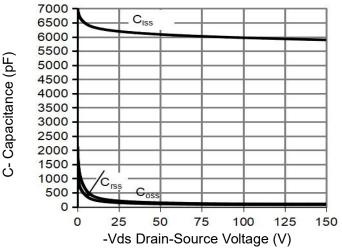


Figure 7 Capacitance vs Vds

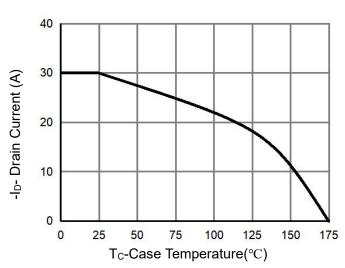


Figure 9 Drain Current vs Case Temperature

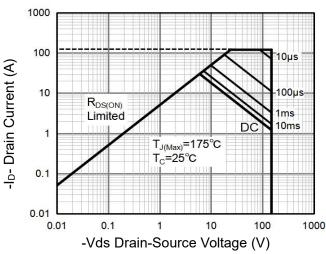


Figure 8 Safe Operation Area

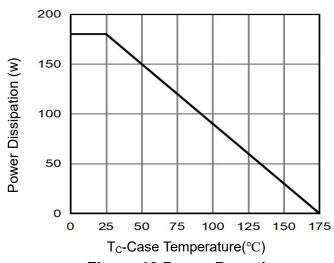
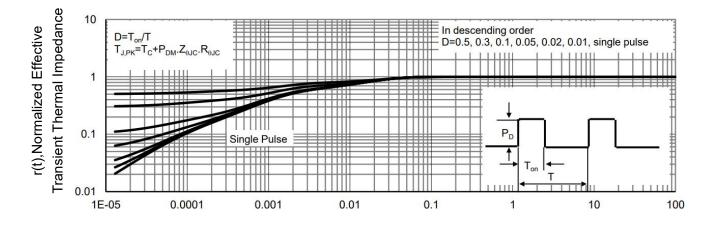


Figure 10 Power De-rating

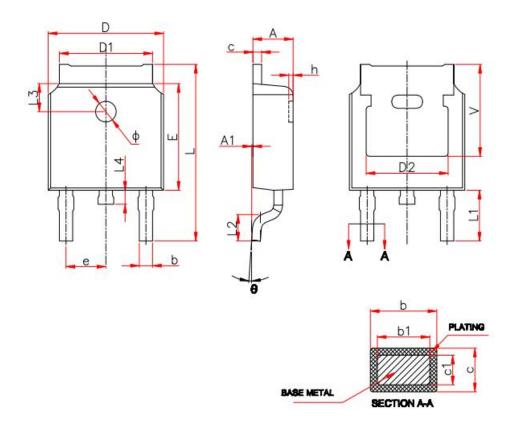


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



Symbol	Millimeters			
Symbol	Min.	Max.		
Α	2.20	2.40		
A1	0.00	0.13		
b	0.66	0.86		
b1	0.73	0.79		
С	0.46	0.58		
c1	0.50	0.52		
D	6.50	6.70		
D1	5.10	5.46		
D2	4.83 REF.			
E	6.00	6.20		
е	2.19	2.39		
L	9.80	10.40		
L1	2.90	REF.		
L2	1.40	1.70		
L3	1.60 REF.			
L4	0.60	1.00		
Ф	1.10	1.30		
θ	0°	8°		
h	0.00	0.30		
V	5.35 REF.			

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